

**isc N-Channel MOSFET Transistor**
**R6530ENZ**
**FEATURES**

- Drain Current  $-I_D = 30A @ T_C = 25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS} = 650V(\text{Min})$
- Static Drain-Source On-Resistance  
:  $R_{DS(on)} = 140m\ \Omega (\text{Max})$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**DESCRIPTION**

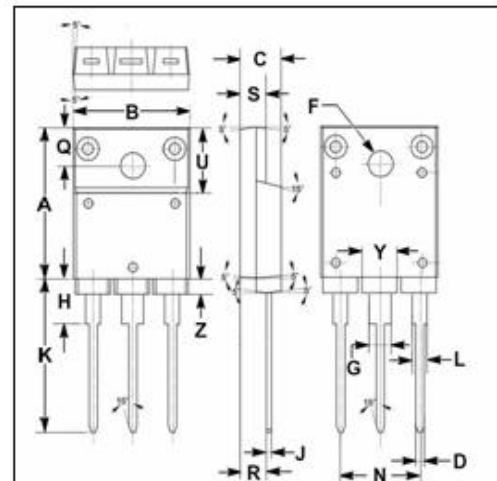
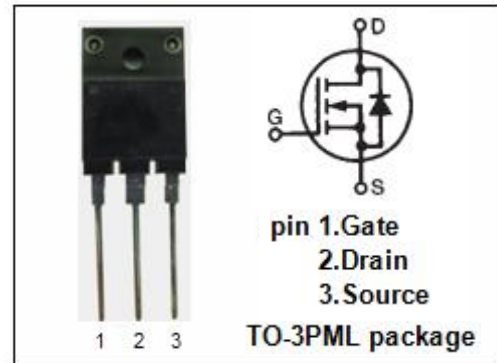
- Designed for use in switch mode power supplies and general purpose applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	650	V
$V_{GS}$	Gate-Source Voltage-Continuous	$\pm 20$	V
$I_D$	Drain Current-Continuous	30	A
$I_{DM}$	Drain Current-Single Pluse	90	A
$P_D$	Total Dissipation @ $T_C = 25^\circ C$	86	W
$T_J$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature	-55~150	$^\circ C$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.5	$^\circ C/W$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.75	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
H	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10

## isc N-Channel MOSFET Transistor

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## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA	650		V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =1mA	2	4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 14.5A		140	mΩ
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V; V <sub>DS</sub> = 0		±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0 V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0@T <sub>J</sub> =125°C		100 1000	μA
V <sub>SD</sub>	Forward On-Voltage	I <sub>S</sub> = 30A; V <sub>GS</sub> = 0		1.5	V

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